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ON Semiconductor®

# FDP027N08B

## N-Channel PowerTrench® MOSFET

80 V, 223 A, 2.7 mΩ

### Features

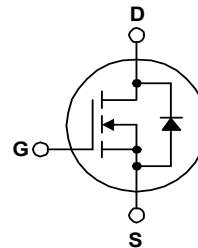
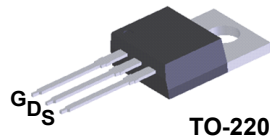
- $R_{DS(on)} = 2.21 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 100 \text{ A}$
- Low FOM  $R_{DS(on)} * Q_G$
- Low Reverse-Recovery Charge,  $Q_{rr} = 112 \text{ nC}$
- Soft Reverse-Recovery Body Diode
- Enables High Efficiency in Synchronous Rectification
- Fast Switching Speed
- 100% UIL Tested
- This device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

### Description

This N-Channel MOSFET is produced using ON Semiconductor's PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

### Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FDP027N08B_F102	Unit
$V_{DSS}$	Drain to Source Voltage	80	V
$V_{GSS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ , Silicon Limited)	223*
		- Continuous ( $T_C = 100^\circ\text{C}$ , Silicon Limited)	158*
		- Continuous ( $T_C = 25^\circ\text{C}$ , Package Limited)	120
$I_{DM}$	Drain Current	- Pulsed (Note 1)	892
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	917
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	6.0
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	246
		- Derate Above $25^\circ\text{C}$	1.64
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

\*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120 A.

### Thermal Characteristics

Symbol	Parameter	FDP027N08B_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.61	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

FDP027N08B — N-Channel PowerTrench® MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP027N08B-F102	FDP027N08B	TO-220	Tube	N/A	N/A	50 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{V}$	80	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.05	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64 \text{V}, V_{GS} = 0 \text{V}$ $V_{DS} = 64 \text{V}, T_C = 150^\circ\text{C}$	-	-	1 500	$\mu\text{A}$
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{V}, V_{DS} = 0 \text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{V}, I_D = 100 \text{A}$	-	2.21	2.7	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10 \text{V}, I_D = 100 \text{A}$	-	227	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 40 \text{V}, V_{GS} = 0 \text{V},$ $f = 1 \text{MHz}$	-	10170	13530	pF
$C_{oss}$	Output Capacitance		-	1670	2220	pF
$C_{rss}$	Reverse Transfer Capacitance		-	35	-	pF
$C_{oss(er)}$	Energy Related Output Capacitance	$V_{DS} = 40 \text{V}, V_{GS} = 0 \text{V}$	-	3025	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 40 \text{V}, V_{GS} = 10 \text{V},$ $I_D = 100 \text{A}$	-	137	178	nC
$Q_{gs}$	Gate to Source Gate Charge		-	56	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	25	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		(Note 4)	-	28	-
ESR	Equivalent Series Resistance (G-S)	$f = 1 \text{MHz}$	-	2.4	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40 \text{V}, I_D = 100 \text{A},$ $V_{GS} = 10 \text{V}, R_G = 4.7 \Omega$	-	47	104	ns
$t_r$	Turn-On Rise Time		-	66	142	ns
$t_{d(off)}$	Turn-Off Delay Time		-	87	184	ns
$t_f$	Turn-Off Fall Time		(Note 4)	-	41	92

### Drain-Source Diode Characteristics

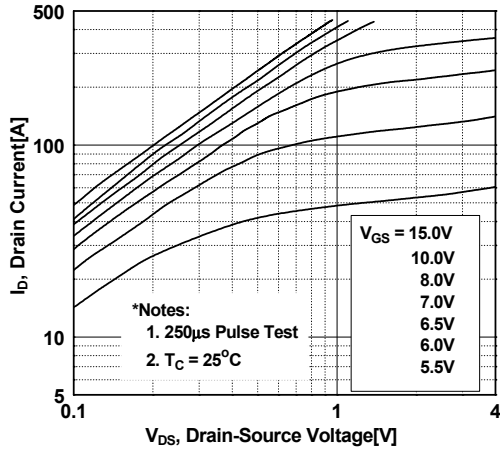
$I_S$	Maximum Continuous Drain to Source Diode Forward Current	-	-	223*	A	
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current	-	-	892	A	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{V}, I_{SD} = 100 \text{A}$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0 \text{V}, V_{DD} = 40 \text{V}, I_{SD} = 100 \text{A},$	-	80	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di_F/dt = 100 \text{A}/\mu\text{s}$	-	112	-	nC

#### Notes:

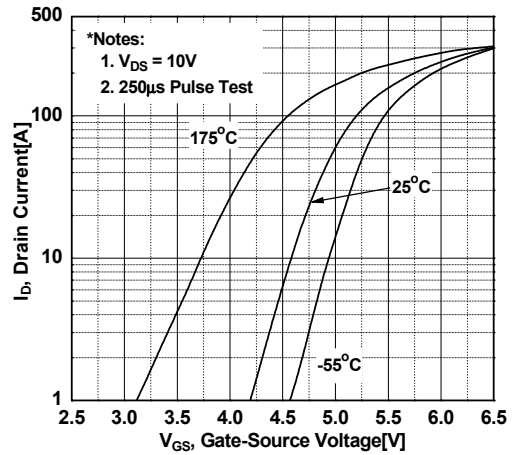
1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $L = 3 \text{mH}, I_{AS} = 24.72 \text{A}, R_G = 25 \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 100 \text{A}, di/dt \leq 200 \text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

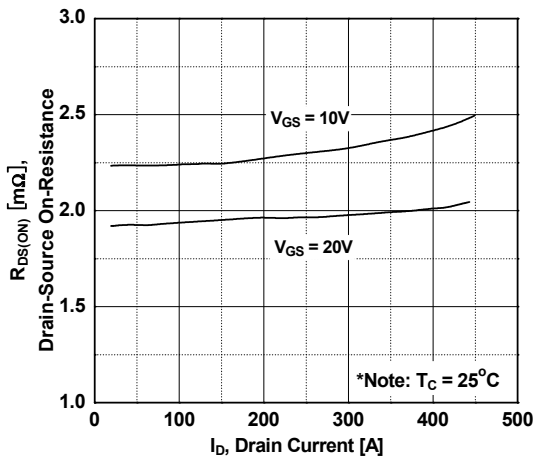
**Figure 1. On-Region Characteristics**



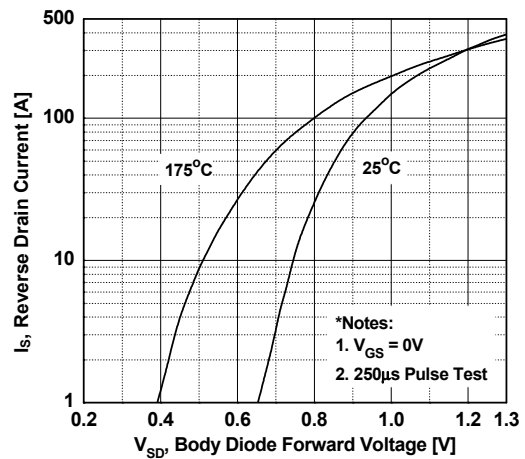
**Figure 2. Transfer Characteristics**



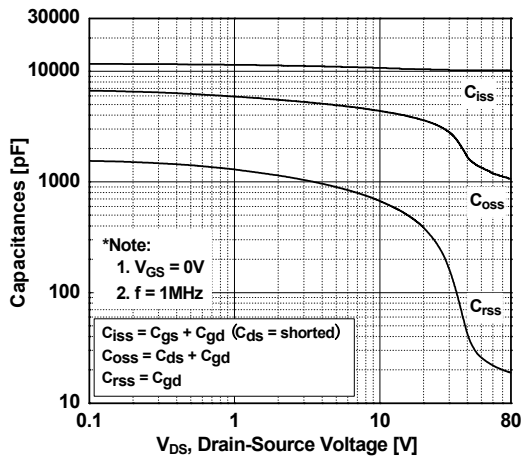
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



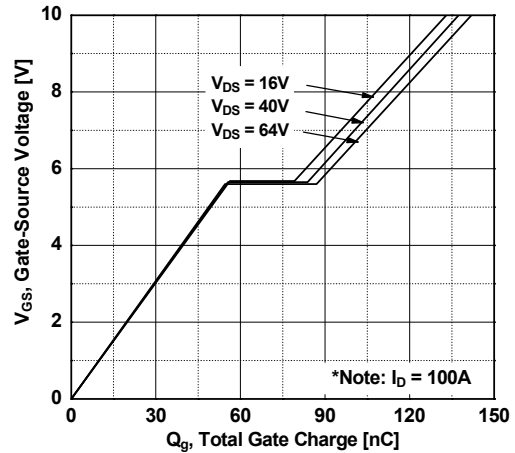
**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**

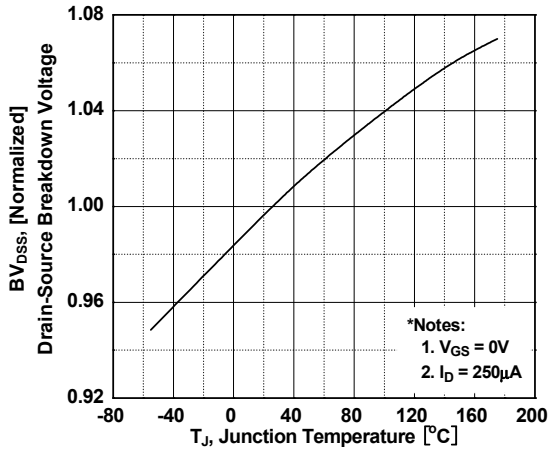


**Figure 6. Gate Charge Characteristics**

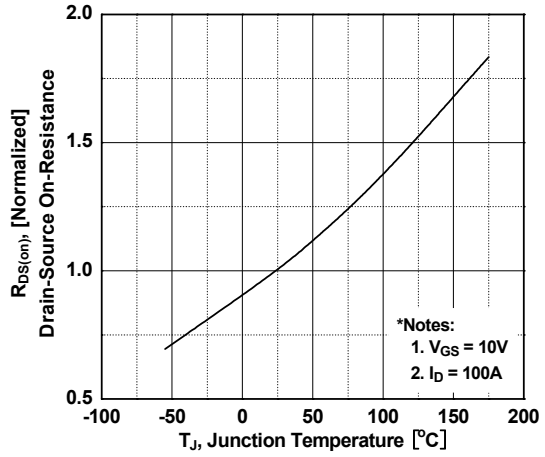


## Typical Performance Characteristics (Continued)

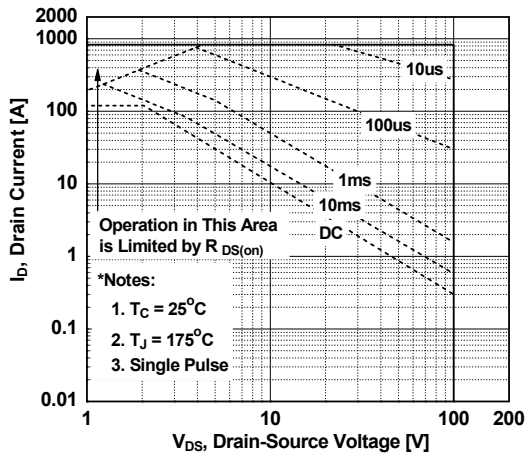
**Figure 7. Breakdown Voltage Variation vs. Temperature**



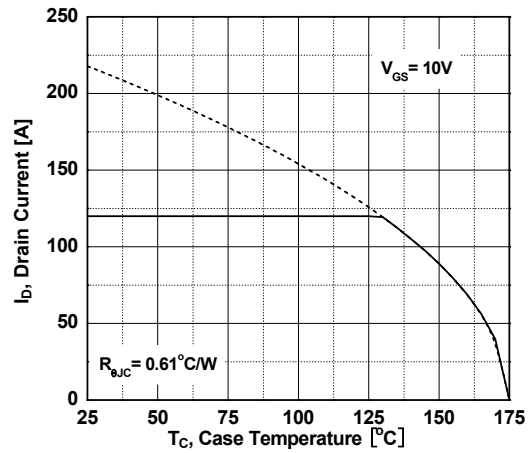
**Figure 8. On-Resistance Variation vs. Temperature**



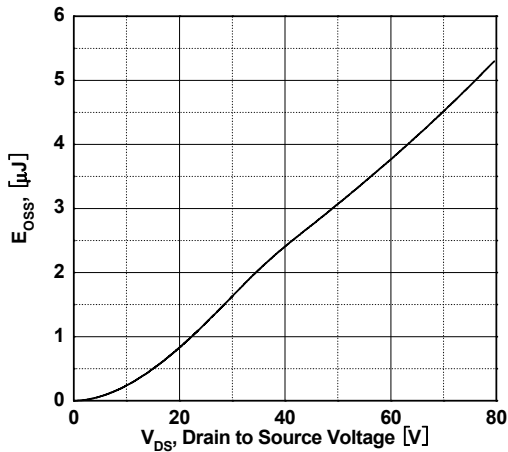
**Figure 9. Maximum Safe Operating Area**



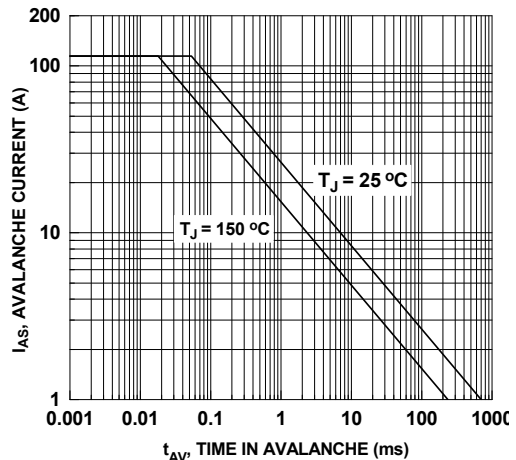
**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. E\_oss vs. Drain to Source Voltage**

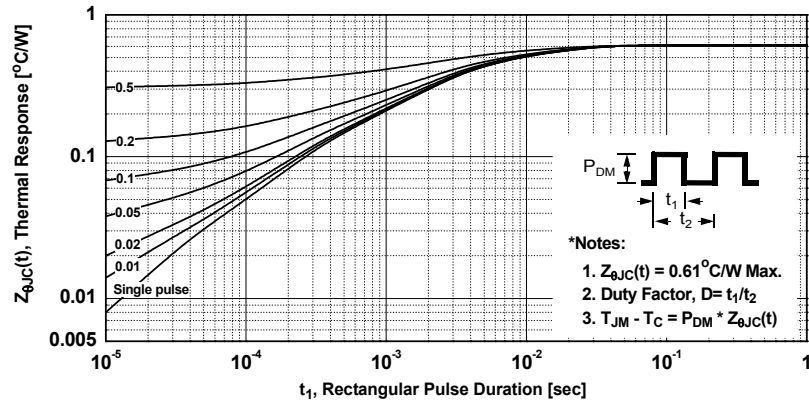


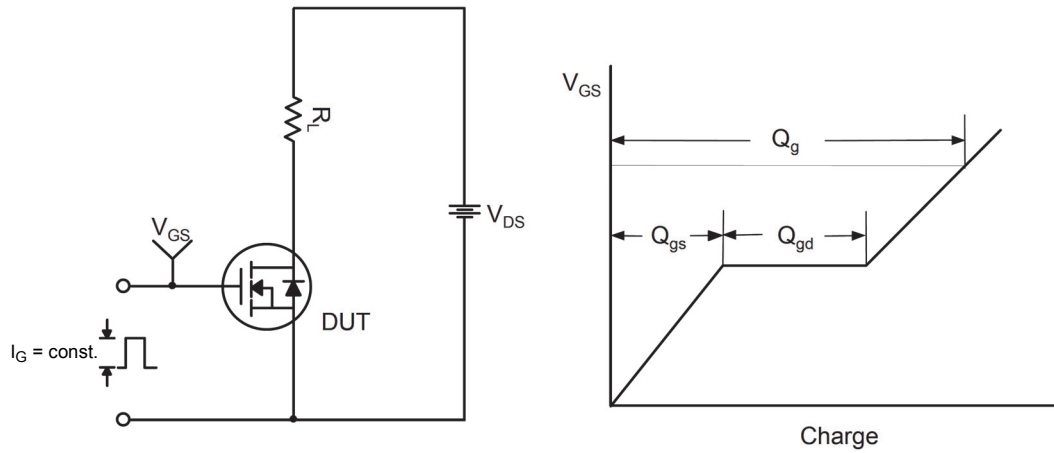
**Figure 12. Unclamped Inductive Switching Capability**



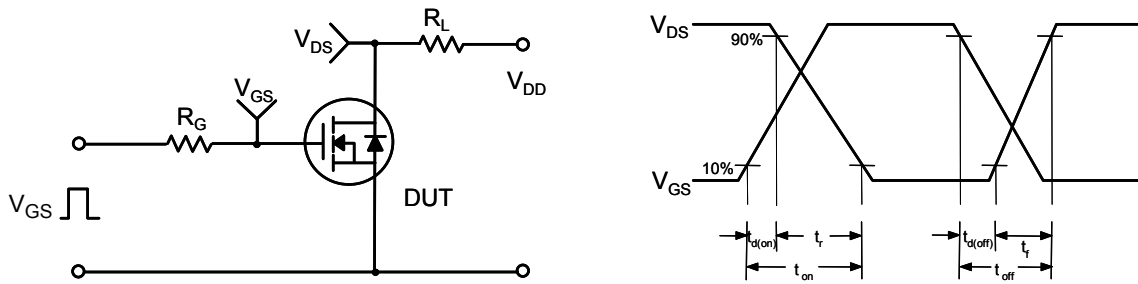
Typical Performance Characteristics (Continued)

Figure 13. Transient Thermal Response Curve





**Figure 14. Gate Charge Test Circuit & Waveform**



**Figure 15. Resistive Switching Test Circuit & Waveforms**



**Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms**

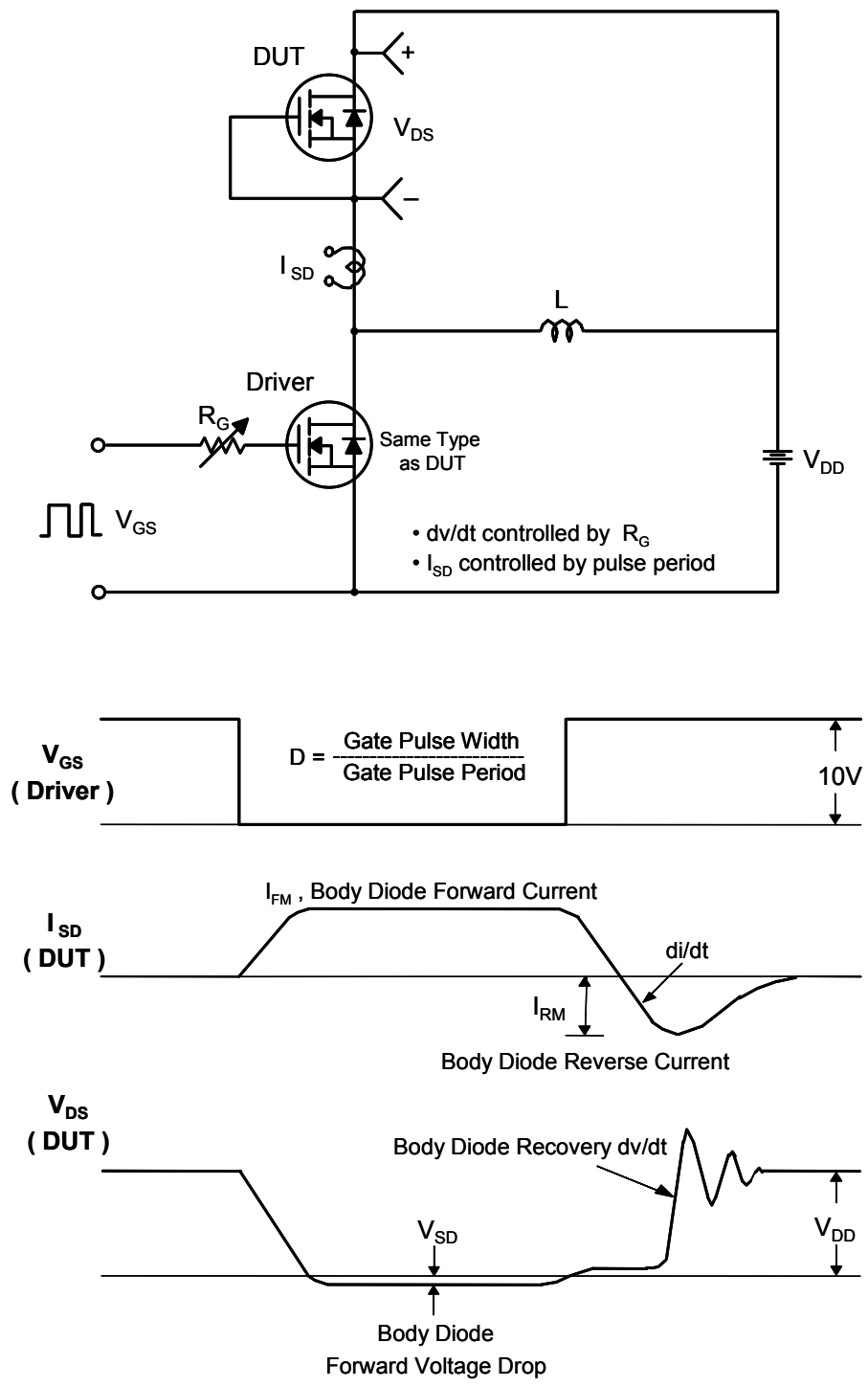
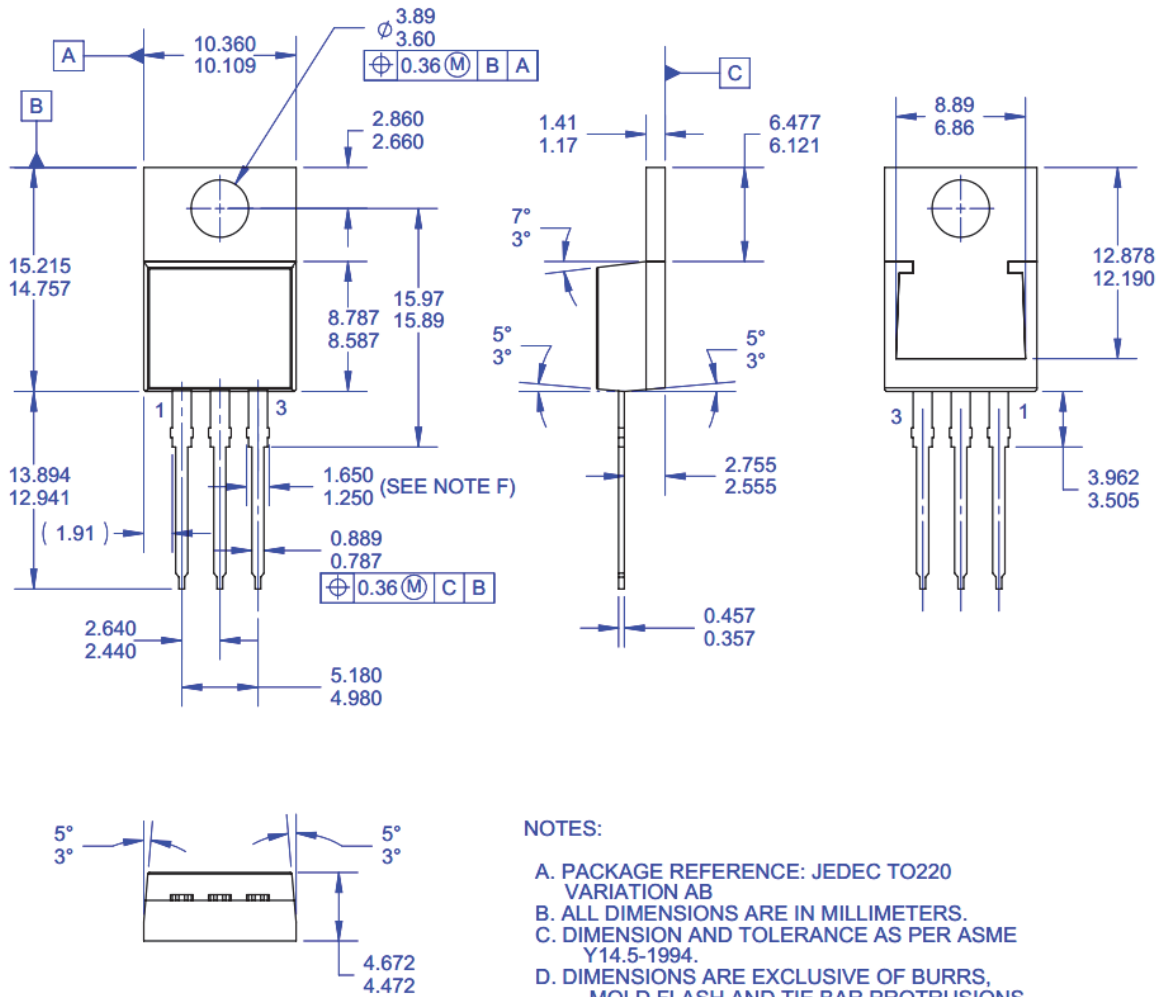


Figure 17. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms



## Mechanical Dimensions



**Figure 18. TO-220, Molded, 3-Lead, Jedec Variation AB (Delta)**

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